

LISTING OF CLAIMS

The following is a copy of Applicant's claims that identifies language being added with underlining ("____") and language being deleted with strikethrough ("---"), as is applicable:

1. (Currently Amended) A semiconductor device comprising:
a first electrode component;
a second electrode component;
a first layer comprising at least a portion of the first electrode component and at least a portion of the second electrode component;
a second layer having a portion comprising deposited semiconductor material contacting the first and second electrode components; and
a third layer comprising a substrate,

wherein the first, second and third layers are arranged in order such that the second layer is positioned between the first layer and the third layer, and

wherein the first and second electrode components comprise electro-deposited metal,

wherein the device is a thin film transistor having a channel in the semiconductor material, a source electrode as the first electrode, a drain electrode as the second electrode, and a gate electrode,

wherein the source, drain and gate electrodes are formed from electro-deposited metal, and

wherein the first layer comprises the source electrode and the drain electrode and the gate electrode lies in a fourth layer between the second layer and the third layer, the semiconductor device further comprising a fifth layer, comprising a continuous dielectric layer, between the fourth layer and the third layer.

2-4. (Cancelled)

5. (Previously Presented) A semiconductor device as claimed in claim 1, wherein the deposited semiconductor material comprises organic semiconductor material.

6. (Cancelled)

7. (Previously Presented) A semiconductor device as claimed in claim 1, wherein the semiconductor material is embedded in the device and overlain by the first layer.

8. (Previously Presented) A semiconductor device as claimed in claim 1 wherein the substrate is flexible.

9-13. (Cancelled)

14. (Currently Amended) A semiconductor device as claimed in claim 10 1, wherein the source and drain electrodes each partially overlap the gate electrode but are separated therefrom by the semiconductor material and a second dielectric material layer.

15-17. (Cancelled).

18. (Currently Amended) A semiconductor device as claimed in claim 9 comprising:

a first electrode component;

a second electrode component;

a first layer comprising at least a portion of the first electrode component and at least a portion of the second electrode component;

a second layer having a portion comprising deposited semiconductor material contacting the first and second electrode components; and

a third layer comprising a substrate,

wherein the first, second and third layers are arranged in order such that the second layer is positioned between the first layer and the third layer,

wherein the first and second electrode components comprise electro-deposited metal,

wherein the device is a thin film transistor having a channel in the semiconductor material, a source electrode as the first electrode, a drain electrode as the second electrode, and a gate electrode,

wherein the source, drain and gate electrodes are formed from electro-deposited metal, and

wherein the first layer comprises a first portion of the source electrode, a first portion of the drain electrode and the gate electrode.

19. (Currently Amended) A semiconductor device as claimed in claim 18, wherein the second layer comprises a second portion of the source electrode contacting the semiconductor material and a second portion of the drain electrode contacting the semiconductor material.

20-21. (Cancelled)

22. (Previously Presented) A semiconductor device as claimed in claim 18, further comprising dielectric material in the second layer between the semiconductor material and the gate electrode in the first layer.

23. (Previously Presented) A semiconductor device as claimed in claim 18, wherein the first layer has a substantially planar surface forming a surface of the semiconductor device incorporating portions of the source, drain and gate electrodes.

24. (Previously Presented) A substrate for a display device comprising a plurality of semiconductor devices as claimed in claim 1.

25-58. (Cancelled)